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PTO/SB/06A (10-01)
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown 10/789,042
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 2815
	Examiner Name	Unknown R. Wilson
Sheet 1 of 7		Attorney Docket No: 1303.050US2

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	Examiner Name	Unknown <u>A. W. Iron</u>
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	Examiner Name	Unknown P. Wilson
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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 3815
	Examiner Name	Unknown A. Wilson
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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 2815
	Examiner Name	Unknown A. WILSON
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A. Wilson

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Group Art Unit	Unknown 2815
Examiner Name	Unknown A. Wilson

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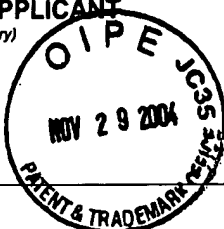
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First Named Inventor	Ahn, Kie
Group Art Unit	2812 2815
Examiner Name	Unknown A. Wilson

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Attorney Docket No: 1303.050US2

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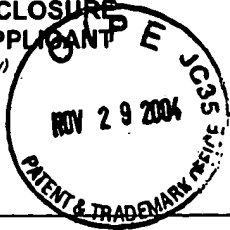
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Attorney Docket No: 1303.050US2

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